



NPN Transistors Array

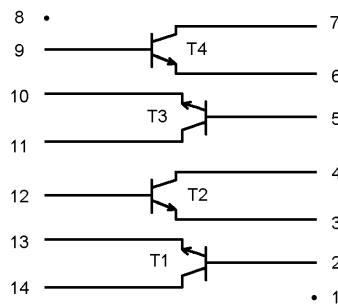
HJ251A

GENERAL DESCRIPTION

The HJ251A is a NPN Transistors Array IC, Pin to pin replaced RUSSIAN IC **1HT251A**. It not only have closely Elec-match and excellent Heat-match but also coherence and uniformity is superior to other discrete circuit. Package is Ceramic Flat 14pin, Reliability and relative stability worked in $-55^{\circ}\text{C} \sim +125^{\circ}\text{C}$.

ELECTRIC PRINCIPLE DIAGRAM

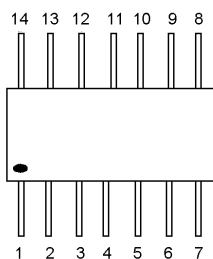
Table 1.



PKG & PIN CONFIGURATION

Table 2.

Ceramic Flat 14pin



Pin NO.	1	2	3	4	5	6	7
FUN	NC	b ₁	e ₂	c ₂	b ₃	e ₄	c ₄
Pin NO.	8	9	10	11	12	13	14
FUN	NC	b ₄	e ₃	c ₃	b ₂	e ₁	c ₁

ABSOLUTE MAXIMUM RATINGS

Voltage of Power Supply: 50V
Operating Temperature: $-55^{\circ}\text{C} \sim +125^{\circ}\text{C}$.

Dissipation Power: 600mW
Junction Temperature: $+175^{\circ}\text{C}$

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ELECTRICAL CHARATERISTICS

-55℃≤T_A≤+125℃ unless otherwise noted.

Table 3.

Parameter	Symbol	Conditions	Ratings			Unit
			Min	Typ	Max	
DC Forward-Current Transfer Ratio	h_{FE}	$V_{CE}=5V$ $I_E=200mA$	30	100	150	
Collector-Cutoff Current	I_{CBO}	$V_{CB}=45V$		0.1	6	A
Collector-Emitter Satiation Voltage	$V_{CE(sat)}$	$I_B=80mA, I_C=400mA$		0.5	1	V
Emitter - Current	I_{EBO}	$V_{EB}=4V$		0.1	10	A
Base- Emitter Satiation Voltage	$V_{BE(sat)}$	$I_B=80mA$			1.2	V
Collector Capacitance	C_C	$V_{CB}=10V, f=5MHz,$ $T_A=+25^{\circ}C$			15	pF
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=0.1mA$	60			V
Current-Gain Bandwidth Product	f_T	$V_{CE}=10V, I_C=3mA$	200			MHz

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